

ABSTRACT OF THE DISCLOSURE

An implanting process for amorphizing a crystalline substrate is proposed according to the present invention. In particular, according to the present invention, amorphous regions are formed in a substrate by exposing the substrate to an ion beam which is kept at a tilt angle between 10 and 80 degrees with respect to the surface of the substrate. Accordingly, ion channeling during subsequent implanting processes is prevented not only in the vertical direction but also in the horizontal direction so that doped regions exhibiting optimum doping profile tailoring may be realized.